



<b>Form 1449 (Modified)</b>		<b>Atty Docket No.</b> <b>LAM1P187/P1216</b>	<b>Application No.:</b> <b>10/798,456</b>
<b>Information Disclosure Statement By Applicant</b>		<b>Applicant:</b> <b>CHOI et al.</b>	
<b>(Use Several Sheets if Necessary)</b>		<b>Filing Date</b> <b>March 10, 2004</b>	<b>Group</b> <b>1765</b>

#### U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
	A1.						

#### Foreign Patent or Published Foreign Patent Application

Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub-class	Translation	
							Yes	No
LTUE	B1.	0050972	05/05/82	EPO	H01L	21/88	X	
LTUE	B2.	0496614	07/29/92	EPO	H01L	21/3105	X	
LTUE	B3.	0553961	08/04/93	EPO	H01L	21/311	X	
LTUE	B4.	0777267	06/04/97	EPO	H01L	21/311	X	
LTUE	B5.	1041614	10/04/00	EPO	H01L	21/306	X	
LTUE	B6.	2000340552	12/08/00	Japan	H01L	21/3065	X	
LTUE	B7.	2001110784	04/20/01	Japan	H01L	21/3065	X	
LTUE	B8.	11-111680	04/23/99	Japan	H01L	21/3065	X	
LTUE	B9.	11-016887	01/22/99	Japan	H01L	21/3065	X	
LTUE	B10.	0889507	01/07/99	EPO	H01L	21/311	X	
LTUE	B11.	0305268	03/01/89	EPO	H01L	21/306	X	

#### Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
LTUE	C1.	Horiike Y. et al., "High Rate and Highly Selective SiO <sub>2</sub> Etching Employing Inductively Coupled Plasma and Discussion on Reaction Kinetics", Journal of Vacuum Science and Technology: Part A, American Institute of Physics, New York, US, Vol. 13, no. 3, Part 1, 1 May 1995, pp. 801-809.
LTUE	C2.	Kumar M.J. et al., "Selective Reactive Ion Etching of PECVD Silicon Nitride over Amorphous Silicon in CF <sub>4</sub> /H <sub>2</sub> and Nitrogen Containing CF <sub>4</sub> /H <sub>2</sub> Plasma Gas Mixtures", Solid State Electronics, Elsevier Science Publishers, Barking, GB, vol. 39, no. 1, 1995, pp. 33-37.
LTUE	C3.	Maeda M. et al., "Low Dielectric Constant Amorphous SiBN Ternary Films Prepared by Plasma-Enhanced Deposition", Japanese Journal of Applied Physics, Publication Office Japanese Journal of Applied Physics, Tokyo, Japan, vol. 26, no. 5, Part 1, 1 May 1987, pp. 660-665.
LTUE	C4.	Norstrom H., "Silicon Surface Damage Caused by Reactive Ion Etching in Fluorocarbon Gas Mixtures Containing Hydrogen", Journal of Vacuum Science and Technology: Part B, American Institute of Physics, New York, US, vol. 9, no. 1, 1991, pp. 34-40.

<b>Examiner</b> /Lynette Umez Eronini/	<b>Date Considered</b> (08/17/2006)
---	--

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<b>Form 1449 (Modified)</b>  <b>Information Disclosure Statement By Applicant</b>  (Use Several Sheets if Necessary)	Atty Docket No.	Application No.:
	LAM1P187/P1216	10/798,456
	Applicant:	
	CHOI et al.	
	Filing Date	Group
	March 10, 2004	1765

LTUE	C5.	Norstrom H. et al., "RIE of SiO <sub>2</sub> in Doped and Undoped Fluorocarbon Plasmas", Vacuum, Pergamon Press Ltd., Great Britian, Vol. 32, No. 12, pp. 737-745; 1982.
LTUE	C6.	Standaert, T.E.F.M. et al., "Patterning of Fluorine-, Hydrogen-, and Carbon-Containing SiO <sub>2</sub> -Like Low Dielectric Constant Materials in High-Density Fluorocarbon Plasmas: Comparison with SiO <sub>2</sub> ", Journal of Vacuum Science and Technology A 173(3), May/June 1999, pp. 741-748.
LTUE	C7.	International Search Report or the Declaration for PCT/US03/18791 dated 01/16/2004.
LTUE	C8.	Written Opinion dated March 2, 2004 for PCT/US03/18791.

Examiner	Date Considered
/Lynette Umez Eronini/	(08/17/2006)

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.